

<b>FORM PTO - 1449</b> <b>INFORMATION DISCLOSURE STATEMENT</b> 				<b>ATTY DOCKET NO.: ASC-049C1</b> <b>APPLICANT: Fitzgerald</b> <b>SERIAL NO.: 10/774,890</b> <b>FILING DATE: February 9, 2004</b> <b>EXAMINER: Tran, Mai Huong C.</b> <b>GROUP: 2818</b>			
<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>MHC</i>	A1	2001/0003364	06/14/2001	Sugawara <i>et al.</i>			
	A2	2002/0024395	02/28/2002	Akatsuka <i>et al.</i>			
	A3	2002/0043660	04/18/2002	Yamazaki <i>et al.</i>			
	A4	2002/0084000	07/04/2002	Fitzgerald			
	A5	2002/0096717	07/25/2002	Chu <i>et al.</i>			
	A6	2002/0100942	08/01/2002	Fitzgerald <i>et al.</i>			
	A7	2002/0123167	09/05/2002	Fitzgerald			
	A8	2002/0123183	09/05/2002	Fitzgerald			
	A9	2002/0125471	09/12/2002	Fitzgerald <i>et al.</i>			
	A10	2002/0168864	11/14/2002	Cheng <i>et al.</i>			
	A11	2003/0003679	01/02/2003	Doyle <i>et al.</i>			
	A12	2003/0013323	01/16/2003	Hammond <i>et al.</i>			
	A13	2003/0034529	02/20/2003	Fitzgerald <i>et al.</i>			
	A14	2003/0057439	03/27/2003	Fitzgerald			
	A15	2003/0102498	06/05/2003	Braithwaite <i>et al.</i>			
	A16	2003/0199126	10/23/2003	Chu <i>et al.</i>			
	A17	2003/0203600	10/30/2003	Chu <i>et al.</i>			
	A18	2003/0215990	11/20/2003	Fitzgerald <i>et al.</i>			
	A19	2003/0218189	11/27/2003	Christiansen			
	A20	2003/0227057	12/01/2003	Lochtefeld <i>et al.</i>			
	A21	2004/0005740	01/01/2004	Lochtefeld <i>et al.</i>			
	A22	2004/0014304	01/22/2004	Bhattacharyya			
<i>↓</i>	A23	2004/0031979	02/19/2004	Lochtefeld			06/06/2003
EXAMINER <i>Mai Huong C.</i>				DATE CONSIDERED <i>09/22/04</i>			

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<b>U.S. PATENT DOCUMENTS</b>								
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
✓	A24	2004/0041210	03/04/2004	Mouli			09/02/2003	
	A25	2004/0075149	04/22/2004	Fitzgerald <i>et al.</i>			07/23/2003	
	A26	4,010,045	03/01/1977	Ruehrwein				
	A27	4,710,788	12/01/1987	Dambkes <i>et al.</i>				
	A28	4,987,462	01/22/1991	Kim <i>et al.</i>				
	A29	4,990,979	02/05/1991	Otto				
	A30	4,997,776	03/05/1991	Harame <i>et al.</i>				
	A31	5,013,681	05/07/1991	Godbey <i>et al.</i>				
	A32	5,155,571	10/13/1992	Wang <i>et al.</i>				
	A33	5,166,084	11/24/1992	Pfiester				
	A34	5,177,583	01/05/1993	Endo <i>et al.</i>				
	A35	5,202,284	04/13/1993	Kamins <i>et al.</i>				
	A36	5,207,864	05/04/1993	Bhat <i>et al.</i>				
	A37	5,208,182	05/04/1993	Narayan <i>et al.</i>				
	A38	5,212,110	05/18/1993	Pfiester <i>et al.</i>				
	A39	5,221,413	06/22/1993	Brasen <i>et al.</i>				
	A40	5,240,876	08/34/1993	Gaul <i>et al.</i>				
	A41	5,241,197	08/31/1993	Murakami <i>et al.</i>				
	A42	5,250,445	10/05/1993	Bean <i>et al.</i>				
	A43	5,285,086	02/08/1994	Fitzgerald				
	A44	5,291,439	03/01/1994	Kauffmann <i>et al.</i>				
✓	A45	5,298,452	03/29/1994	Meyerson				
✓	A46	5,310,451	05/10/1994	Tejwani <i>et al.</i>				
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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
MM	A47	5,316,958	05/31/1994	Meyerson			
	A48	5,346,848	09/13/1994	Grupen-Shemansky <i>et al.</i>			
	A49	5,374,564	12/20/1994	Bruel			
	A50	5,399,522	03/21/1995	Ohori			
	A51	5,413,679	05/09/1995	Godbey			
	A52	5,424,243	06/13/1995	Takasaki			
	A53	5,426,069	06/20/1995	Selvakumar <i>et al.</i>			
	A54	5,426,316	06/20/1995	Mohammad			
	A55	5,442,205	08/15/1995	Brasen <i>et al.</i>			
	A56	5,461,243	10/24/1995	Ek <i>et al.</i>			
	A57	5,461,250	10/24/1995	Burghartz <i>et al.</i>			
	A58	5,462,883	10/31/1995	Dennard <i>et al.</i>			
	A59	5,476,813	12/19/1995	Naruse			
	A60	5,479,033	12/26/1995	Baca <i>et al.</i>			
	A61	5,484,664	01/16/1996	Kitahara <i>et al.</i>			
	A62	5,523,243	06/04/1996	Mohammad			
	A63	5,523,592	06/04/1996	Nakagawa <i>et al.</i>			
	A64	5,534,713	07/09/1996	Ismail <i>et al.</i>			
	A65	5,536,361	07/16/1996	Kondo <i>et al.</i>			
	A66	5,540,785	07/30/1996	Dennard <i>et al.</i>			
	A67	5,572,043	11/05/1996	Shimizu <i>et al.</i>			
	A68	5,596,527	01/21/1997	Tomioka <i>et al.</i>			
✓	A69	5,617,351	04/01/1997	Bertin <i>et al.</i>			

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<b>U.S. PATENT DOCUMENTS</b>								
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
<i>WT</i>	A70	5,630,905	05/20/1997	Lynch <i>et al.</i>				
	A71	5,659,187	08/19/1997	Legoues <i>et al.</i>				
	A72	5,683,934	11/04/1997	Candelaria				
	A73	5,698,869	12/16/1997	Yoshimi <i>et al.</i>				
	A74	5,714,777	02/03/1998	Ismail <i>et al.</i>				
	A75	5,728,623	03/17/1998	Mori				
	A76	5,739,567	04/14/1998	Wong				
	A77	5,759,898	06/02/1998	Ek <i>et al.</i>				
	A78	5,777,347	07/07/1998	Bartelink				
	A79	5,786,612	07/28/1998	Otani <i>et al.</i>				
	A80	5,786,614	07/28/1998	Chuang <i>et al.</i>				
	A81	5,792,679	08/11/1998	Nakato				
	A82	5,808,344	09/15/1998	Ismail <i>et al.</i>				
	A83	5,847,419	12/08/1998	Imai <i>et al.</i>				
	A84	5,877,070	03/02/1999	Goesele <i>et al.</i>				
	A85	5,891,769	04/06/1999	Liaw <i>et al.</i>				
	A86	5,906,708	05/25/1999	Robinson <i>et al.</i>				
	A87	5,906,951	05/25/1999	Chu <i>et al.</i>				
	A88	5,912,479	06/15/1999	Mori <i>et al.</i>				
	A89	5,943,560	08/24/1999	Chang <i>et al.</i>				
	A90	5,963,817	10/05/1999	Chu <i>et al.</i>				
	A91	5,966,622	10/12/1999	Levine <i>et al.</i>				
	A92	5,998,807	12/07/1999	Lustig <i>et al.</i>				
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U.S. PATENT DOCUMENTS								
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
✓ A93		6,013,134	01/11/2000	Chu <i>et al.</i>				
	A94	6,030,887	02/29/2000	Desai <i>et al.</i>				
	A95	6,030,889	02/29/2000	Aulicino <i>et al.</i>				
	A96	6,033,974	03/07/2000	Henley <i>et al.</i>				
	A97	6,033,995	03/07/2000	Muller				
	A98	6,058,044	05/02/2000	Sugiura <i>et al.</i>				
	A99	6,059,895	05/09/2000	Chu <i>et al.</i>				
	A100	6,074,919	06/13/2000	Gardner <i>et al.</i>				
	A101	6,096,590	08/01/2000	Chan <i>et al.</i>				
	A102	6,103,559	08/15/2000	Gardner <i>et al.</i>				
	A103	6,107,653	08/22/2000	Fitzgerald				
	A104	6,111,267	08/29/2000	Fischer <i>et al.</i>				
	A105	6,117,750	09/12/2000	Bensahel <i>et al.</i>				
	A106	6,130,453	10/10/2000	Mei <i>et al.</i>				
	A107	6,133,799	10/17/2000	Favors <i>et al.</i>				
	A108	6,140,687	10/31/2000	Shimomura <i>et al.</i>				
	A109	6,143,636	11/07/2000	Forbes <i>et al.</i>				
	A110	6,153,495	11/28/2000	Kub <i>et al.</i>				
	A111	6,154,475	11/28/2000	Soref <i>et al.</i>				
	A112	6,160,303	12/12/2000	Fattaruso				
	A113	6,162,688	12/19/2000	Gardner <i>et al.</i>				
✓	A114	6,184,111	02/06/2001	Henley <i>et al.</i>				
✓	A115	6,191,007	02/20/2001	Matsui <i>et al.</i>				
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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
11t	A116	6,191,432	02/20/2001	Sugiyama <i>et al.</i>				
	A117	6,194,722	02/27/2001	Fiorini <i>et al.</i>				
	A118	6,204,529	03/20/2001	Lung <i>et al.</i>				
	A119	6,207,977	03/27/2001	Augusto				
	A120	6,210,988	04/03/2001	Howe <i>et al.</i>				
	A121	6,218,677	04/17/2001	Brockaert				
	A122	6,232,138	05/15/2001	Fitzgerald <i>et al.</i>				
	A123	6,235,567	05/22/2001	Huang				
	A124	6,242,324	06/05/2001	Kub <i>et al.</i>				
	A125	6,249,022	06/19/2001	Lin <i>et al.</i>				
	A126	6,251,755	06/26/2001	Furukawa <i>et al.</i>				
	A127	6,261,929	07/17/2001	Gehrke <i>et al.</i>				
	A128	6,266,278	07/24/2001	Harari <i>et al.</i>				
	A129	6,271,551	08/07/2001	Schmitz <i>et al.</i>				
	A130	6,271,726	08/07/2001	Fransis <i>et al.</i>				
	A131	6,291,321	09/18/2001	Fitzgerald				
	A132	6,313,016	11/06/2001	Kibbel <i>et al.</i>				
	A133	6,316,301	11/13/2001	Kant				
	A134	6,323,108	11/27/2001	Kub <i>et al.</i>				
	A135	6,329,063	12/11/2001	Lo <i>et al.</i>				
	A136	6,335,546	01/01/2002	Tsuda <i>et al.</i>				
	A137	6,339,232	01/15/2002	Takagi				
✓	A138	6,350,993	02/26/2002	Chu <i>et al.</i>				
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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
<i>MF</i>	A139	6,352,909	03/05/2002	Usenko				
	A140	6,368,733	04/09/2002	Nishinaga				
	A141	6,372,356	04/16/2002	Thornton <i>et al.</i>				
	A142	6,372,593	04/16/2002	Hattori <i>et al.</i>				
	A143	6,399,970	06/04/2002	Kubo <i>et al.</i>				
	A144	6,403,975	06/11/2002	Brunner <i>et al.</i>				
	A145	6,407,406	06/18/2002	Tezuka				
	A146	6,420,937	07/16/2002	Akatsuka <i>et al.</i>				
	A147	6,425,951	07/30/2002	Chu <i>et al.</i>				
	A148	6,429,061	08/06/2002	Rim				
	A149	6,521,041	02/18/2003	Wu <i>et al.</i>				
	A150	6,524,935	02/25/2003	Canaperi <i>et al.</i>				
	A151	6,555,839	04/29/2003	Fitzgerald				
	A152	6,573,126	06/03/2003	Cheng <i>et al.</i>				
	A153	6,583,015	06/24/2003	Fitzgerald <i>et al.</i>				
	A154	6,593,191	07/15/2003	Fitzgerald				
	A155	6,593,641	07/15/2003	Fitzgerald				
	A156	6,602,613	08/05/2003	Fitzgerald				
	A157	6,603,156	08/05/2003	Rim				
	A158	6,646,322	11/11/2003	Fitzgerald				
	A159	6,649,480	11/18/2003	Fitzgerald <i>et al.</i>				
	A160	6,677,192	01/13/2004	Fitzgerald				
	A161	6,703,144	03/09/2004	Fitzgerald			03/18/2003	
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<b>U.S. PATENT DOCUMENTS</b>									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
<i>MH</i>	A162	6,703,688	03/09/2004	Fitzgerald			07/16/2001		
	A163	6,709,903	03/23/2004	Christiansen			04/30/2003		
	A164	6,713,326	03/30/2004	Cheng <i>et al.</i>			03/04/2003		
	A165	6,723,661	04/20/2004	Fitzgerald			07/16/2001		
	A166	6,724,008	04/20/2004	Fitzgerald			07/16/2001		
	A167	6,730,551	05/04/2004	Lee <i>et al.</i>			08/02/2002		
	A168	6,737,670	05/18/2004	Cheng <i>et al.</i>			03/07/2003		
<i>✓</i>	A169	6,750,130	06/15/2004	Fitzgerald			01/07/2001		
<b>FOREIGN PATENT DOCUMENTS</b>									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
<i>MH</i>	B1	41 01 167	07/23/1992	DE				N	Y (Abstract only)
	B2	0 514 018	11/19/1992	EP				N	Y
	B3	0 587 520	03/16/1994	EP				N	Y
	B4	0 683 522	11/22/1995	EP				N	Y
	B5	0 828 296	03/11/1998	EP				N	Y
	B6	0 829 908	03/18/1998	EP				N	Y
	B7	0 838 858	04/29/1998	EP				N	Y (Abstract only)
	B8	1 020 900	07/19/2000	EP				N	Y
	B9	1 174 928	01/23/2002	EP				N	Y
	B10	2 701 599	09/01/1993	FR				Y	Y
	B11	2 342 777	04/19/2000	GB				N	Y
	B12	61/141116	06/28/1986	JP				N	Y (Abstract only)
<i>✓</i>	B13	2/210816	08/22/1990	JP				N	Y (Abstract only)
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FOREIGN PATENT DOCUMENTS									
EXAM .INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
144	B14	3/036717	02/18/1991	JP				N	Y
	B15	4-307974	10/30/1992	JP				N	Y (Abstract only)
	B16	5-166724	07/23/1993	JP				N	Y (Abstract only)
	B17	6-177046	06/24/1994	JP				N	Y (Abstract only)
	B18	6-244112	09/02/1994	JP				Y	Y
	B19	6-252046	09/09/1994	JP				Y	Y
	B20	7-094420	04/07/1995	JP				N	Y (Abstract only)
	B21	7-106446	04/21/1995	JP				Y	Y
	B22	7-240372	09/12/1995	JP				Y	Y
	B23	10-270685	10/09/1998	JP				N	Y
	B24	11-233744	08/27/1999	JP				N	Y (Abstract only)
	B25	2000-021783	01/21/2000	JP				N	Y
	B26	2000-031491	01/28/2000	JP				Y	Y
	B27	2001-319935	11/16/2001	JP				N	Y
	B28	2002-076334	03/15/2002	JP				N	Y
	B29	2002-164520	06/07/2002	JP				N	Y
	B30	2002-289533	10/04/2002	JP				N	Y
	B31	98/59365	12/30/1998	WO				N	Y
	B32	99/53539	10/21/1999	WO				N	Y
	B33	00/48239	08/17/2000	WO				N	Y
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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE

## FOREIGN PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
MM	B34	00/54338	09/14/2000	WO				N	Y
	B35	01/22482	03/29/2001	WO				N	Y
	B36	01/54202	07/26/2001	WO				N	Y
	B37	01/93338	12/06/2001	WO				N	Y
	B38	01/99169	12/27/2001	WO				N	Y
	B39	02/13262	02/14/2002	WO				N	Y
	B40	02/15244	02/21/2002	WO				N	Y
	B41	02/27783	04/04/2002	WO				N	Y
	B42	02/47168	06/13/2002	WO				N	Y
	B43	02/071488	09/12/2002	WO				N	Y
	B44	02/071491	09/12/2002	WO				N	Y
	B45	02/071495	09/12/2002	WO				N	Y
	B46	02/082514	10/17/2002	WO				N	Y
	B47	04/006311	01/15/2004	WO				N	Y
MM	B48	04/006327	01/15/2004	WO				N	Y

## OTHER ART, JOURNAL ARTICLES, ETC.

EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)		
MM	C1	Armstrong <i>et al.</i> , "Design of Si/SiGe Heterojunction Complementary Metal-Oxide-Semiconductor Transistors," IEDM Technical Digest (1995 International Electron Devices Meeting), pp. 761-764.	

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✓	C84	Sakaguchi <i>et al.</i> , "ELTRAN by splitting porous Si layers," Proceedings of the 195th Int. SOI Symposium, Electrochemical Society, Vol. 99-3 (1999), pp. 117-121.							
EXAMINER <i>Mai Huong C.</i>				DATE CONSIDERED <i>09/22/04</i>					

FORM PTO - 1449 INFORMATION DISCLOSURE STATEMENT					ATTY DOCKET NO.: ASC-049C1 APPLICANT: Fitzgerald SERIAL NO.: 10/774,890 FILING DATE: February 9, 2004 EXAMINER: Tran, Mai Huong C. GROUP: 2818				
U.S. PATENT DOCUMENTS									
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FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
MF	C85	Schäffler, "High-Mobility Si and Ge Structures," <u>Semiconductor Science and Technology</u> , Vol. 12 (1997), pp. 1515-1549.							
1	C86	Sugimoto <i>et al.</i> , "A 2V, 500 MHz and 3V, 920 MHz Low-Power Current-Mode 0.6 $\mu$ m CMOS VCO Circuit," <u>Institute of Electronics, Information and Communication Engineers</u> , Vol. E82-C, No. 7 (July 1999), pp. 1327-1329.							
	C87	Terman <i>et al.</i> , "Metal Gate Strained Silicon MOSFETs for Microwave Integrated Circuits," <u>IEEE</u> (October 2000), pp. 38-43.							
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	C94	Welser, "The Application of Strained-Silicon/Relaxed-Silicon Germanium Heterostructures to Metal-Oxide-Semiconductor Field-Effect Transistors," Ph.D. Thesis, Stanford University, Dept. of Electrical Engineering (1994), pp. 1-127.							
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<b>OTHER ART, JOURNAL ARTICLES, ETC.</b>									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
<i>MH</i>	C95	Wolf <i>et al.</i> , <u>Silicon Processing for the VLSI Era, Vol. 1: Process Technology</u> , Lattice Press, Sunset Beach, CA, (1986), pp. 384-386.							
	C96	Xie <i>et al.</i> , "Semiconductor Surface Roughness: Dependence on Sign and Magnitude of Bulk Strain," <u>Physical Review Letters</u> , Vol. 73, No. 22 (November 28, 1994), pp. 3006-3009.							
	C97	Xie <i>et al.</i> , "Very high mobility two-dimensional hole gas in Si/Ge <sub>x</sub> Si <sub>1-x</sub> /Ge structures grown by molecular beam epitaxy," <u>Applied Physics Letters</u> , Vol. 63, No. 16 (October 18, 1993), pp. 2263-2264.							
	C98	Xie, "SiGe field effect transistors," <u>Materials Science and Engineering</u> , Vol. 25 (1999), pp. 89-121.							
	C99	Yamagata <i>et al.</i> , "Bonding, Splitting and Thinning by Porous Si in ELTRAN; SOI- Epi Wafer," <u>Material Research Society Symposium Proceedings</u> , Vol. 681E (2001), pp. 18.2.1-18.2.10							
	C100	Yeo <i>et al.</i> , "Nanoscale Ultra-Thin-Body Silicon-on-Insulator P-MOSFET with a SiGe/Si Heterostructure Channel," <u>IEEE Electron Device Letters</u> , Vol. 21, No. 4 (April 2000), pp. 161-163.							
	C101	Zhang <i>et al.</i> , "Demonstration of a GaAs-Based Compliant Substrate Using Wafer Bonding and Substrate Removal Techniques," <u>IEEE</u> (1998), pp. 25-28.							
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